How Can Computer Simulations Contribute to Understand the Static Structure of G lasses?

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Introduction: The M olecular D ynam ics M ethod

M any di erent com putational techniques are denoted as \com puter sin ulation", from \m acroscopic" techniques, such as nite elem ent m ethods to calculate m echanical properties, to \m icroscopic" techniques that deal with nuclei and electrons to calculate the electronic structure of m aterials (e.g., the density functional m ethod [1]). However, in the present article we m ean by structure the geom etric arrangem ent of atom s considering typical length scales from 0.2 A to 20 A. In particular, we are interested in how this geom etric structure depends on the chem ical constituents (SiO₂, B₂O₃, :::), therm odynam ic variables (tem perature T, pressure p), cooling history by which the glass was prepared, etc. As input to such a simulation on the atom istic scale, one w ishes to take a suitable force eld that describes the interaction between the atom s, treating them like point particles in classical mechanics. O f course, this neglect of all quantum e ects is a severe lim itation of the approach that we are going to describe, and in principle it can be avoided by m ore accurate m ethods: the C ar-P arrinello m ethod [2] com bines m olecular dynam ics

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with the density functional treatment of electronic structure which depends properly on the coordinates of the nuclei, and thus avoids the approximations inherent in the force eld to some extent | the path integral M onte C arlo m ethod [3] takes into account the H eisenberg uncertainty principle (i.e., the fact that one cannot specify precisely simultaneously positions and m om enta of the nuclei, since the latter are spread out over a region of the order of the de B roglie wavelength), and thus allows a correct treatment of the therm all properties of solids at low tem peratures.

A lthough the application of either technique to materials like SiO₂ may yield promising results in the near future, we can ne ourselves here to the molecular dynamics (MD) methods in the framework of classical statistical mechanics [4]. Unlike the techniques proposed more recently [2,3], applications of MD to simulate glasses have been developed since a long time [5], and we feel that recent applications [6,7] allow a rather precise and detailed description of both the structure and the them al properties of glasses.

Basically, the MD simulation tries to m in ic the experimental procedure by which a glass is produced from the melt that is cooled down su ciently fast to bypass crystallization. However, as will be discussed below, an important di erence between experiments and simulations is that in the MD method cooling rates are many orders of magnitude faster than in reality, and these extremely fast cooling schedules do have an e ect on the physical properties of the \glass" observable in such a \com puter experiment" [6]. To bypass this di culty, there are actually m any attempts to directly create the am orphous structure of silica glass or other so-called \continuous random networks" by direct construction [8]. For example, one uses topological rules (e.g. in am orphous SiO₂ each silicon atom has to have four oxygen atom s as neighbors, each oxygen atom has to have two silicon atom s as neighbors, the length of the covalent Si{O -bond is taken as constant and used as an input parameter) but allows for some disorder (e.g. the angles between covalent bonds are taken from some ad-hoc chosen distributions which are often optim ized to m atch the experim ental radial pair distribution function [8]). We feel, however, that despite its successes to reproduce certain known facts about the geom etrical structure of glasses this heuristic approach su ers from unknown (and hence uncontrolled)

errors, unlike M D which | in the fram ework of classical statistical mechanics | is a $\$ rst principles"-method. We also mention that an alternative $\$ rst principles"-method is M onte C arb sampling [9]. There one generates con gurations of the model system distributed according to the canonical distribution function of statistical mechanics, i.e. proportional to exp(H=k_BT) where H is the H am iltonian and k_B is the Boltzmann's constant. While this method is widely used, particularly for suitably coarse grained models, where many of the atom istic degrees of freedom are disregarded, it does not seem to o er any particular advantage for the atom istic simulation of inorganic glasses. Hence this technique will not be described here either.

Basic Features of a M olecular D ynam ics Program : an Introduction for the N ovice

The equations of motions that are solved in elementary MD are Newton's equations for N atom s with Cartesian coordinates fr_{ig} , i = 1, ..., N, r_{i} being the gradient operator with respect to r_{i} ,

$$\mathbf{m}_{i}\mathbf{r}_{i} = \mathbf{r}_{i}\mathbf{U} \quad \mathbf{f}_{i}; \quad \mathbf{v}_{i} \quad \mathbf{r}_{i} = d\mathbf{r}_{i} = d\mathbf{t}; \tag{1}$$

where m_i is the mass of particle i and f_i is the force on atom i, derived from the potential energy function U of the system,

$$U(\mathbf{r}_{1};\mathbf{r}_{2};\ldots;\mathbf{r}_{N}) = \bigcup_{\substack{i=1 \ j>i}}^{N} (\mathbf{j}\mathbf{r}_{i} \quad \mathbf{r}_{j}\mathbf{j}):$$
(2)

In Eq.(2) we have made the approximation that U is simply the sum of pair potentials between atoms, which clearly will not be true in general, but which greatly simplies the calculations since then the force f_i simply becomes

$$\mathbf{f}_{i} = \begin{pmatrix} \mathbf{x}^{N} & 0 \\ 0 \\ \mathbf{y}_{i} \in \mathbf{i} = 1 \end{pmatrix} = 0 \\ \mathbf{r}_{i} = \begin{pmatrix} \mathbf{x}^{N} \\ \mathbf{y}_{j} \end{pmatrix} = 0 \\ \mathbf{r}_{i} = \mathbf{f}_{ij} :$$
(3)

In fact, it is not at allobvious that the directional covalent bonds in m aterials such as SiO₂, B₂O₃ etc. can be reliably m odelled by Eq.(2), and indeed potentials are sometimes used that explicitly include three-body terms that keep a bond angle close to its equilibrium value $_0$, e.g. [10, 11]

$$u = \frac{1}{2}K (_{0})^{2}:$$
 (4)

However, while in the case of B_2O_3 even inclusion of terms such as Eq.(4) still does not allow a fully satisfactory modelling of glassy structures [11], in the case of SiO₂ the situation seems to be fortunately much simpler, and a pairwise potential proposed by van Beest et al. [12], henceforth referred to as \BKS potential", already gives reliable results [6,13,14]. With the abbreviation $r_{ij} = jr_i r_j j$ the BKS potential is given by

$$u(r_{ij}) = q_i q_j e^2 = r_{ij} + A_{ij} exp(B_{ij} r_{ij}) C_{ij} r_{ij}^6 \text{ with } i; j 2 \text{ fSiOg:}$$
 (5)

Here e is the charge of an electron. Note that q_b and q_{bi} are e ective charges, i.e. are given by 1:2 and 2.4, respectively (q_{bi} + 2 q_b = 0 is required because of charge neutrality, of course). A part from this (pseudo-) C oulom b interaction between every pairs of atom s, the only short range interactions present are the ones between Si{O pairs and O {O pairs, with parameters A_{00} 1389 eV, A_{SD} 18004 eV, B_{00} 2:76 A¹, B_{SD} 4:873 A¹, and C_{00} = 175 eV A⁶, C_{SD} 133:6 eV A⁶ [3.12].

As is well-known, Newton's equations conserve the total energy E = U + K, where K is the kinetic energy,

$$K = \sum_{i=1}^{X^{N}} \frac{1}{2} m_{i} \cong^{2} :$$
 (6)

If one solves these equations numerically for a (closed) system of N atoms in a box of volum eV, one generates a trajectory through phase space from which one can compute the time average of various physical observables. Since E, N, V are sed one therefore realizes the microcanonical ensemble of statistical mechanics. Since we deal with classical statistical mechanics, temperature T can be inferred from the equipartition theorem and thus, if the system is in therm al equilibrium throughout the MD \run", we have

$$\overline{K} = 3N k_B T = 2:$$
(7)

(By a barwe henceforth denote the time average along the trajectory.) Similarly, pressure can be computed from the virial theorem

$$p = \frac{1}{V} \left(N k_{B} T + (1=3) \sum_{i=1}^{N} \frac{1}{r_{i}} \frac{1}{r_{i}} \right)$$
(8)

In statistical mechanics, one often wishes to use an ensemble where V and T or p and T rather than V and E are the given independent variables. W hile in the therm odynamic

limit these various ensembles yield equivalent results, for nite N systematic di erences occur. Furtherm ore it is also in portant to note that any time average \overline{A} can be estimated only to within a certain \statistical error", because of the nite time span covered by the M D run. Thus generalizations of M D for the microcanonical ensemble to these other ensembles are useful and widely used (in \constant pressure" MD one needs to couple the system to a piston, in \constant temperature" MD to a therm ostat, etc. [4]). For derivations and details about these extensions, we refer to the literature [4]. Here we only mention another aspect related to the nite size of the simulated system, and this is the aspect of boundary conditions on the surface of the simulation box (which for uids and am orphous systems usually is taken of cubic shape, $V = L^3$, where L is the linear dimension of the box). Since one is typically interested in bulk behavior of the simulated material, and one wishes to work with only about 10^3 to 10^4 atoms due to lim ited com puter resources, it is crucial to make disturbances due to these boundaries as small as possible. This is achieved by using periodic boundary condition, i.e. the box is surrounded by identical in ages of itself centered at all integer multiples of L (when the center of the original box is taken as the origin of the coordinate system) and thus the system becomes quasi-in nite. Of course, only the particles in the central box are independent and need to be handled by Newton's equations, but if a particle leaves the box through, say, the surface on its right, the next in age of that particle enters the box from the left. W hile these surfaces thus have no physical e ects whatsoever, i.e. surface e ects are completely eliminated, it is important to realize that e ects associated with the niteness of N are still present. With respect to therm odynamic properties, such nite size e ects are well known (e.g. \rounding" of phase transitions [9]), but one must also be aware that the dynamics of the system may be a ected as well (e.g. a phonon mode traveling to the right may re-enter the box from the left and interfere with itself, etc. [15]).

The periodic boundary condition must also be correctly treated when one considers interactions among distant particles. For slow ly decaying potentials, such as the C oulom b part in Eq.(5), it is essential to sum the interactions not only over all particles in the

prim ary box but also over all the periodic in ages | every atom interacts thus with an in nite number of in ages of all the other particles! This seem ingly di cult task, however, is e ciently solved by the Ewald method [4]. For the short range part, however, one may even follow the simpler strategy to cut the potential o if the distance r exceeds a maximum distance r_{max} (e.g., for the 0 {0 -interaction in [6] $r_{max} = 5.5$ A could be used since then the strength of the potential has decreased to about 1 % of its value at the preferred 0 {0 distance}.

As a last point, we emphasize that integration of Newton's equations, Eq.(1), for a many-particle system of interest cannot be done exactly, but only approximately, due to the niteness of the time step t of the numerical integration procedure. By making t su ciently small this error can be made as small as desired | but then it becomes increasingly di cult to propagate in time up to time scales of physical interest. Thus it is in portant to choose a \good" integration algorithm. Several suitable algorithm s exist, but here only the standard Verlet algorithm is quoted [4], which is correct up to order $(t)^3$,

$$\mathbf{r}_{i}(t + t) = \mathbf{r}_{i}(t) + t\mathbf{v}_{i}(t) + \frac{1}{2m_{i}}(t)^{2}\mathbf{f}_{i}(t);$$
 (9)

$$\mathbf{v}_{i}(t+t) = \mathbf{v}_{i}(t) + \frac{t}{2m_{i}}[\mathbf{f}_{i}(t) + \mathbf{f}_{i}(t+t)]$$
: (10)

Note that the propagation of the velocities, Eq.(10), requires that the forces are known both at the present tim e t and at the next tim e step t+ t, which can of course be calculated from \mathbf{r}_1 (t + t) using Eq.(3). This algorithm is time reversible and conserves the phase space volum e of a continuous set of phase space points, as is required for time averaging in statistical mechanics [4]. Nevertheless, it is clearly necessary that t is at least about two orders of magnitude smaller than the time constant of elementary physical motions in the system, e.g. vibration times of covalent Si(O-bonds or bond angles, which are significantly less than one pico second: Therefore it becomes necessary to choose a time-step t as small as t = 1:6 10¹⁵ secto get reliable results! Thus even very long MD runs (several millions of time steps) can span only a very short interval of physical time, of the order of 10 nano sec. This is not only true for SiD₂ but for MD simulations of atom istic models of real materials in general. While experimental techniques such as neutron scattering

[16] are constrained to a similarly restricted \observation time window", the important distinction is that in MD the same short time scale is available not only for observation but also for the equilibration of the structure. Therefore the way how a structure for an am orphous material studied by MD was prepared needs careful attention | although this is an obvious point, it offen is \swept under the rug" in the literature!

For example in the results described in the next section, this preparation of the system "was done by making rst an MD run of 40,000 time steps at an initial tem perature $T_i = 7000$ K. This length is more than enough to equilibrate the system at this extremely high tem perature. Subsequently the system was cooled, at zero pressure, by coupling it to a heat bath whose tem perature $T_{b}(t)$ was decreased linearly in time, $T_{b}(t) = T_{i}$ t, from 1:14 10^{15} K/s to 4:44 10^{12} K/s. Even the slowest cooling with cooling rates rate is many orders of magnitude larger than the ones used in the laboratory. However, it is currently not possible to simulate a quench of the system with cooling rates that are signi cantly sm aller than the ones used here, since for the sm allest cooling rate one simulation run of the system (which contained 334 Si-and 6680 -atom s in the central box) needs already about 340 h of CPU time on an IBM RS6000/370 workstation, and one needs to take a sam ple average over at least 10 independent runs (starting from di erent initial con gurations) to improve the statistical accuracy of the \sim ulation data".

A Case Study: Cooling-R ate D ependence of the Structure of am orphous SiO₂ Here we brie y review some typical results that were recently obtained by Vollm ayr et al. [6]. As an example for macroscopic properties we show in Fig. 1 the temperature dependence of the density for the di erent cooling rates studied. One sees that, at very high temperatures, all curves (apart from the ones for the three fastest cooling rates) fall onto a master curve, the equilibrium curve. However, for the fastest cooling rates the system falls out of equilibrium during the cooling process in mediately, demonstrating that even at extrem ely high temperatures such runs do not give any reliable inform ation on the therm al equilibrium behavior of the system .

The curves corresponding to the smallest cooling rates show a maximum at around

4800 K, i.e. a density anomaly. Qualitatively, but not quantitatively, this anomaly is in agreement with experiment (the experimental value for the temperature of the density maximum is considerably lower, namely 1820 K [17]). It is unlikely that this quantitative discrepancy is related to the too fast cooling since the location of the maximum is independent of the cooling rate, if the latter is su ciently small. More probably the discrepancy rejects an inaccuracy of the potential. However, for different potentials this density anomaly is present only at even higher temperatures or not present at all [18]: thus nothing would be gained by using instead of Eq.(5) one of these (typically more complicated) alternative potentials.

For interm ediate and sm all values of , the density decreases upon cooling (after having passed the maximum) and reaches a minimum. At even lower temperatures the curves become, within the accuracy of our data, straight lines with negative slope. The value of this (positive) therm al volum e expansion coe cient decreases with decreasing cooling rate from about $_{p}$ 7 10 6 K 1 for = 1:14 10 15 K/s to $_{p}$ 2:5 10 6 K 1 for = $4.44 \quad 10^{15}$ K/s. Experimental values at and above room temperature are [17] 0:55 10⁶ K¹. Note, however, that quantum statistical mechanics requires that q $_{p}$ (T ! 0) ! 0, i.e. the density must reach its groundstate value with vanishing slope. This feature can never be reproduced by a purely classical calculation such as MD. In fact deviations from classical statistical mechanics are expected at tem peratures of the order of the Debye tem perature, which is roughly T 1200 K in SiO₂ [19]. A similar caveat also applies to the speci c heat C_p , which reaches in the MD simulation [6] at low tem peratures a value of about 1.25 J/gK, close to the value of the classical D ulong-Petit law (which would yield 1.236 J/gK): classical M D (as well as classical M onte C arlo) can never reproduce the vanishing of the speci c heat as T ! 0. (In principle, this can be achieved by the quantum -m echanical path integral M onte C arb m ethod β but this approach has so far only been applied to crystals and not yet to glasses.)

W hile experimentally [19] C_p rises rather sharply at the glass transition temperature from about 1.23 J/gK to about 1.5 J/gK, the simulation yields a sm ooth increase at about T = 3000 K to a maximum value of C_p^{max} 2 J/gK near T = 4000 K; the latter behavior

is thus not backed by experiment and may partially be due to artifacts of the too rapid cooling and partially due to inadequacies of the potential [5].

A librough the M D simulation of m olten SiO₂ using the BKS potential gives neither at very high temperatures nor at low temperatures a quantitatively accurate description of them all properties (density, speci c heat, etc.), it nevertheless gives a very good description of the geometric structure of the glass. This is evident if one examines the radial distribution functions g (r) between species and , Fig. 2 (see Ref. [20] for theoretical background on this quantity). One recognizes that with decreasing cooling rate the structural order at short and intermediate distances (i.e. r 8 A) increases, since the peaks and minim a of g (r) become more pronounced. The height of the rstnearest-neighbor peak changes by about 20 %! The am ount of this change is signi cantly larger than any change observed form acroscopic properties [6] and thus we conclude that microscopic properties can show a much stronger dependence on the cooling rate than the m acroscopic properties do.

From Fig. 2 one also sees that although the height of the various peaks shows a signi cant cooling-rate dependence, the location of the peaks is a ected much less by the variation of . Thus it is reasonable to compare these positions with experimental data, indicated in broken lines. E.g., M ozzi and W arren [21] quoted for the location of the 1^{st} and 2^{nd} peak 1.62, 4.15; 2.65, 4.95; 3.12, 5.18 A for SiD, OO and SiSi, respectively. A lthough the agreement is not perfect, the BKS potential does quite well to reproduce the short and medium-range order of silica glass. Note that this potential was developed to describe the crystalline modi cations of SiD₂, and in Ref. [6] it was used for am orphous SiD₂ without adjusting any parameter whatsoever.

Similar conclusions emerge from a discussion of the partial structure factors S (g) [6], where q is the scattering wavenumber, which is the structural quantity that is most directly accessible in direction experiments. But the advantages of the simulation is that full microscopic details of the structure are much more easily accessible. Since Fig. 2 shows that the location $r_{m in}$ of the rst minimum in the radial distribution function is practically independent of (namely $r_{m in}^{SiSi} = 3:42 \text{ A}$, $r_{m in}^{SiO} = 2:20 \text{ A}$, and $r_{m in}^{OO} = 3:00 \text{ A}$), one can compute unambiguously the (partial) coordination number z of particle i by de ning z as the number of other particles $j w \pm j \neq_j = r_i j < r_{m in}$. Fig. 3 shows $P^{z=n}$, the probability that a particle of type has n nearest neighbors of type . The vast majority of silicon atoms are surrounded by z = 4 oxygens; the case z = 5 occurs for the fast cooling rate with probability 5 % and decreases to about 0.5 % probability for the slowest cooling rate. Sim ilarly z = 2 dom inates for oxygens. Thus the BKS potential autom atically yields the \nules" commonly postulated for ideal am orphous SiD₂, nam ely that this system is a \continuous random network" with these coordination numbers z = 4for Si and z = 2 for 0 [8].

M ore disorder, however, is found on an interm ediate length scale: while each SiO₄ tetrahedron is surrounded by four other tetrahedra on average, even for the smallest cooling rate the probability $P_{SiSi}^{z=5}$ is still about 1.5%, and $P_{00}^{z=6}$ increases only from about 0.6 to 0.87 with decreasing cooling rate, over the accessible range of (about 10% of the oxygen atom s have seven other oxygen atom s as second nearest neighbors instead of six). The spread in these next-nearest neighbor coordinations in the network is a clear indication of disorder.

This disorder also show s up clearly in the distribution functions of various bond angles (F ig. 4). It is remarkable that the distribution P_{OSiO} () has its maximum at an angle close to the value of an ideal tetrahedron (109.47), and that the width of this distribution clearly narrow s with decreasing cooling rate. As far as experimental data on the peak positions of these angular distributions and their halfwidths are available at all, the simulations for the slow est cooling rate are already very close to the experimental values. This shows that such simulations can give quite reliable information on such quantities.

A nother characteristic of the medium range order in glasses, that is much discussed in the literature, is the distribution of the frequency of rings of a given size. A ring is de ned as follows: starting from a Si atom one chooses two dierent 0 atoms that are nearest neighbors. Pick one of these. In general this 0 atom will also be a nearest neighbor of a second Si atom. From this new Si atom one then picks a new nearest-neighbor 0 atom, etc. This process is continued until one returns to the 0 atom which is the second one

of the nearest-neighbor 0 atom s of the rst Si-atom. In this way one has constructed a closed loop of Si{0 segments. The shortest one of these loops is called the ring associated with the original Si atom and the two nearest-neighbor 0 -atom s. The num ber of Si{0 segments in this loop is called the size n of this ring.

Fig. 5 shows P (n), the probability that a ring has length n, as function of the cooling rate. As expected, the case n = 6 dom inates, and P (n) for small n (n = 3;4) clearly decrease with decreasing . Note that in -cristobalite (the rst crystalline phase reached from the liquid) only n = 6 occurs, while the lower-tem perature phases -tridym ite and -quartz have rings with both n = 6 and n = 8, but no odd-num bered rings. The large numbers of rings with n = 5 and n = 7 can be considered as a hallmark of am orphous silica, and the di culty to elim inate these \defects" from the structure prevents the system to crystallize easily.

Concluding rem arks

In the previous subsection, it was demonstrated (choosing the work [6] as an example) that with the slowest cooling rates just available, it is now possible to create $\langle \text{good}^{"} \text{ am orphous silica structures, which agree surprisingly well with experimental noings, despite the fact that the simulated cooling rate exceeds the experimental one by many orders of magnitude. However, clear discrepancies remain when one considers the temperature dependence of various quantities, because rst of all the system falls out of equilibrium at a much higher temperature than in the experiment, and secondly because quantum e ects are missing and they are expected to become increasingly in portant at low tem – peratures. O fcourse, we expect that, if the length scales we consider increase, we will not a stronger dependence of the medium range order on the cooling rates, some evidence in this direction was already discussed here, and the more the simulated model will di er from reality (since quantitative inform ation on properties like the ring statistics, F ig. 5, is not available from experiment, this expected discrepancy is not yet detectable in practice: pair correlations g (r) or structure factors S (q) simply are too insensitive probes of am orphous structures!).$

Nevertheless, the rich inform ation from the M D simulation on a large variety of structural properties fg (r), partial coordination numbers, bond angle distributions, ring statistics, etc.g, and the dependence of these properties on both tem perature and cooling rate, allows to correlate these properties with each other and thus to gain insight into how and why the am orphous structure form s. W e feel that this insight still m ay be partially unraveled, and additional studies are desirable (including studies with other potentials that have been used in the literature).

O ne m a jor challenge, of course, is the extension of these studies from pure SiO₂ to silicate glasses that contain m ore components. O ne obvious obstacle to simulate, say, a m ixture of SiO₂ and B_2O_3 is that presently the interaction of a pair of oxygen in SiO₂ is modelled by a completely di erent function [12] than in B_2O_3 [10,11]. But promising is steps to model more-component glasses such as sodium silicate glasses have been taken a long time ago [22], and we think time is ripe to resume such e orts.

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Figure 1: Density of simulated SiO_2 vs. bath temperature T_b , for all cooling rates investigated. The solid and dashed bold curves are the smallest and largest cooling rates , respectively. Note the presence of a local maximum in at temperatures around 4800 K if is small. From Vollmayr et al. [6].





Figure 2: Radial distribution functions of simulated am orphous SiD₂. (a) g_{SiSi}(r). Main gure: the slowest (solid curve) and fastest (dashed curve) cooling rate. The vertical dotted lines give the position of the peak as determined from experiments (see text). Inset: enlargement of the second-nearest neighbor peak for four selected cooling rates.
(b) g_{SiD} (r) and g_{DO} (r) for the slowest (solid curves) and fastest (dashed curves) cooling rate. Inset: enlargement of the second-and third-nearest-neighbor peak. From Vollmayr et al. [6].





Figure 3: Probabilities of partial coordination numbers $P^{z=n}$ plotted vs. cooling rate, for Si{O pairs (a) and O {Sipairs (b). Note the di erent scales for the various curves. From Vollmayr et al. [6].





Figure 4: D istribution function of various angles at several cooling rates in am orphous SiO_2 at T = 0. (a) Angle O-SiO for all cooling rates studied. The vertical line is the experimental value [21]. (b) Angles O-O-O, SiSiSi and SiO-Si for the slowest (solid curves) and fastest (dashed curves) cooling rates investigated. Vertical lines are experimental values from di erent authors (see [6] for details.). From Vollmayr et al. [6].



Figure 5: Probability P (n) that a particle is a member of a ring of size n, plotted vs. . From Vollmayr et al. [6].